L Number	Hits	Search Text	DB	Time stamp
1	0	@ad<=20011206 and 'O' adj1 'SiON' adj1 'N' adj1 'SiON' adj1 'O'	USPAT; US-PGPUB; EPO; JPO;	2003/11/24 13:56
2	0	@ad<=20011206 and 'O/SiON/N/SiON/O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24 13:56
3	1	@ad<=20011206 and 'O-SiON-N-SiON-O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24 13:56
-	696	(438/400).ccls. and @ad<=20011206	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17 11:22
-	6	((438/400).ccls. and @ad<=20011206) and ONO	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 11:26
-	0	@ad<=20011206 and 'ONO structure' with 'buffer layer'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/24
-	290	@ad<=20011206 and 'ONO structure'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/24 11:33
-	160	<pre>@ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/17
-	3	@ad<=20011206 and 'ONO structure' and 'buffer layer'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:40
-	1	@ad<=20011206 and 'multi dielectric layer' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:43
-	26	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/24 11:47
-	0	@ad<=20011206 and 'O-SiON-N-SiON-O'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:49
-	1393	@ad<=20011206 and oxide and SiON and Nitride and SiON and oxide	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17
-	0	@ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/17 12:56
	atory 1	1/24/02 2:25:07 PM Poge 1	IBM TDB	

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-	300		USPAT;	2003/11/24
		with 'nitride' with 'SiON' with 'oxide'	US-PGPUB;	11:28
			EPO; JPO;	
	ļ		DERWENT;	
			IBM TDB	
-	107	(@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/06/19
		with 'nitride' with 'SiON' with 'oxide')	US-PGPUB;	14:52
		and memory	EPO; JPO;	i
		-	DERWENT;	
			IBM TDB	
_	540	@ad<=20011206 and (438/778).ccls.	USPAT;	2002/05/17
		(111, 111, 111, 111, 111, 111, 111, 111	US-PGPUB;	14:32
			EPO; JPO;	111.32
			DERWENT;	
			IBM TDB	1
_	2862	((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
	2002		1	
		or (438/794) or (438/400) or	US-PGPUB;	08:49
		(438/769-770) or (438/770) or	EPO; JPO;	
	1	(438/775)).CCLS.	DERWENT;	
			IBM_TDB	
-	2356	((257/324) or (257/314-315) or (257/406)	USPAT;	2003/11/24
]	or (257/410)).CCLS.	US-PGPUB;	11:50
	1		EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	7	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	08:59
]		(438/769-770) or (438/770) or	EPO; JPO;	
1	1	(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	1
	1	'silane' with 'nitrogen oxide'	IBM TDB	
-	6328	(((438/778) or (438/787) or (438/790-791))	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:03
		(438/769-770) or (438/770) or	EPO; JPO;	5.05
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
1	1	'SiON' or 'silicon oxynitride'	· ·	
l _	0		IBM_TDB	2002/10/22
1 -		1 ((()0-), (0) 02 (200), (0)	USPAT;	2002/10/28
1	1	or (438/794) or (438/400) or	US-PGPUB;	09:04
1		(438/769-770) or (438/770) or	EPO; JPO;	1
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
	_	SiH4 with N2O with NH3	IBM_TDB	
-	8	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:09
1	1	(438/769-770) or (438/770) or	EPO; JPO;	1
1		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
['SiON' with 'deposition'	IBM_TDB	
-	448	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:11
	[(438/769-770) or (438/770) or	EPO; JPO;]
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;]
ţ	Į i	'ammonia'	IBM TDB	Į t
-	190	(((438/778) or (438/787) or (438/790-791)	USPAT;	2002/10/28
		or (438/794) or (438/400) or	US-PGPUB;	09:11
i		(438/769-770) or (438/770) or	EPO; JPO;	
		(438/775)).CCLS.) and @ad<=20011206 and	DERWENT;	
		'ammonia' and 'silane'	IBM TDB	
_	194	@ad<=20011206 and 'ammonia' and 'silane'	USPAT;	2002/10/28
	1,74	and 'nitrogen oxide'	US-PGPUB;	09:16
\)	and nicrogen oxide		09.10
			EPO; JPO;]
			DERWENT;	
	3.50	And c-20011206 and 1-odd 1-odd 1-odd 1-odd	IBM_TDB	0000/00/10
-	359	@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/02/13
		with 'nitride' with 'SiON' with 'oxide'	US-PGPUB;	13:27
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	/
-	27	<pre>@ad<=20011206 and 'ammonia' same 'silane'</pre>	USPAT;	2002/10/28
		same 'nitrogen oxide'	US-PGPUB;	09:19
	[EPO; JPO;	[
	ļ		DERWENT;	
			IBM TDB	1

-	0	@ad<=20011206 and 'oxide' same 'silane'	USPAT;	2003/02/13
		same dichloro adj silane with 'nitrogen	US-PGPUB;	13:29
		oxide'	EPO; JPO;	
			DERWENT; IBM TDB	
_	0	@ad<=20011206 and 'silane' same 'dichloro	USPAT;	2003/02/13
		silane' with 'nitrogen oxide'	US-PGPUB;	13:30
		a == more masses of the contract	EPO; JPO;	20,00
			DERWENT;	
			IBM TDB	
-	3		USPAT;	2003/02/13
		'dichlorosilane' with 'N.sub.20'	US-PGPUB;	13:36
			EPO; JPO;	
			DERWENT;	
1_	0	@ad<=20011206 and 'silicon oxide' same	IBM_TDB USPAT;	2002/02/12
		'silane' same 'DCS' same 'N.sub.20'	US-PGPUB;	2003/02/13
		STITUTE Same Des Same W.Sub.20	EPO; JPO;	13.37
			DERWENT;	
			IBM TDB	
_	32	@ad<=20011206 and 'silicon oxide' same	USPAT;	2003/02/13
		'silane' same 'N.sub.20'	US-PGPUB;	13:39
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	25		USPAT;	2003/06/19
	1	'silane' same 'nitrous oxide' and	US-PGPUB;	10:17
	1	'dichlorosilane'	EPO; JPO; DERWENT;	
			IBM TDB	
_	71	@ad<=20011206 and 'oxide' same 'silane'	USPAT;	2003/06/19
		same 'nitrous oxide' same	US-PGPUB;	10:51
		'dichlorosilane'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12		USPAT;	2003/06/19
		'SiH.sub.4' same 'N.sub.20' same	US-PGPUB;	10:29
		'SiH.sub.2Cl.sub.2'	EPO; JPO;	
i			DERWENT;	
1_	4	@ad<=20011206 and 'silicon oxide' same	IBM_TDB USPAT;	2003/06/19
-	4	'SiH.sub.4' same 'N.sub.20' same	US-PGPUB;	10:37
	1	'SiH.sub.2Cl.sub.2'	EPO; JPO;	10.57
		5111.543.251.543.2	DERWENT;	
	1		IBM TDB	1
-	5	(("6127255") or ("5811316") or	USPAT;	2003/06/19
	1	("5331191") or ("5202275")).PN.	US-PGPUB;	10:37
	1		EPO; JPO;	
			DERWENT;	1
		0.4 (20011206	IBM_TDB	2002/06/22
_	27	<pre>@ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same</pre>	USPAT;	2003/06/20
		same 'nitrous oxide' same 'dichlorosilane'	US-PGPUB;	09:06
	1	dichiolositane	EPO; JPO; DERWENT;	
			IBM TDB	
_	160	(@ad<=20011206 and 'oxide' with 'SiON'	USPAT;	2003/06/19
		with 'nitride' with 'SiON' with 'oxide')	US-PGPUB;	15:20
		and memory	EPO; JPO;	
		<u>-</u>	DERWENT;	
			IBM_TDB	
-	1	"5506178".PN.	USPĀT	2003/06/19
		had a second and a second a second and a second a second and a second		15:06
-	45	hisatomi-kiyoshi.in.	USPAT;	2003/11/24
			US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT; IBM TDB	
_	20	toshiba.as. and 'ONO' and 'oxynitride'	USPAT;	2003/06/19
			US-PGPUB;	15:28
1			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
				

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-	341	toshiba.as. and 'oxynitride'	USPAT;	2003/06/19
			US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT;	
_	16	@ad<=20011206 and 'silicon oxynitride'	IBM_TDB USPAT;	2003/06/20
1	10	same 'silane' same 'dichlorosilane'		09:09
		Same Straine Same dichiolositane	US-PGPUB; EPO; JPO;	09.09
			DERWENT;	
			IBM TDB	
_	2	@ad<=20011206 and 'SiON' same 'silane'	USPAT;	2003/06/20
	_	same 'dichlorosilane'	US-PGPUB;	09:07
		bamo aroniorobirane	EPO; JPO;	""
			DERWENT;	İ
			IBM TDB	
-	45	hisatomi-kiyoshi.in.	USPAT;	2003/11/24
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	@ad<=20011206 and 'oxide' adj2 'SiON'	USPAT;	2003/11/24
		adj2 'nitride' adj2 'SiON' adj2 'oxide'	US-PGPUB;	11:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	9	USPAT;	2003/11/24
		layer'	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT;	
	000		IBM_TDB	
-	296	* · · · · · · · · · · · · · · · · · · ·	USPAT;	2003/11/24
		layer'	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT; IBM TDB	
_	271	@ad<=20011206 and 'multi' adj2	USPAT;	2003/11/24
	2/1	'dielectric' and 'memory'	US-PGPUB;	11:46
		dielectic and memory	EPO; JPO;	11.40
			DERWENT;	
			IBM TDB	
1 _	19	@ad<=20011206 and 'multi' adj1	USPAT;	2003/11/24
		'dielectric' same 'memory'	US-PGPUB;	11:46
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	34		USPAT;	2003/11/24
		'dielectric' and 'memory'	US-PGPUB;	11:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	496	@ad<=20011206 and (257/324).ccls.	USPAT;	2003/11/24
			US-PGPUB;	11:51
			EPO; JPO;	
			DERWENT;	
	124	0-d<-20011206 and (420/016) =-1-	IBM_TDB	2002/11/24
-	134	@ad<=20011206 and (438/216).ccls.	USPAT;	2003/11/24
1			US-PGPUB;	13:33
			EPO; JPO;	
1			DERWENT; IBM TDB	
_	147	@ad<=20011206 and (438/621).ccls.	USPAT;	2003/11/24
1	1 17	caa	US-PGPUB;	11:52
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	<u> </u>		<u>, ====</u> ===	